

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	98	'metal oxide' with 'physical vapor deposition' with 'chemical vapor deposition'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:01
L5	272	(438/785).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:21
L6	646	(257/310).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:22
L7	493	(257/410).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:22
L8	679	(438/778).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:22
L9	452	(438/758).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:22
L10	492	(257/411).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:23
L11	696	(438/240).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:23
L12	118	(438/216).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:23
L13	294	(438/591).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:23

L14	774	(438/585).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:23
L15	696	(438/240).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:23
S1	69	(438/722).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/13 11:07
S2	69	((438/722).CCLS.) and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/21 15:27
S3	223162	"438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 16:06
S4	35716	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113") and 'dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/14 14:15
S5	4864	((438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113") and 'dielectric') and 'mosfet'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/14 14:12
S6	1	((("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113") and 'dielectric') and 'mosfet') and 'group IV metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/14 14:14
S7	16571	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113") and 'dielectric layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/14 14:21
S8	61	((438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113") and 'dielectric layer') and 'hafnium' and 'lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/08/27 16:46
S9	104	((438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113") and 'dielectric') and 'hafnium' and 'lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/14 14:25

S10	36	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113") and 'dielectric') and 'amorphous oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/14 14:26
S11	1	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113") and 'dielectric') and 'hafnium' and 'lanthanum' and 'amorphous oxides'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/14 14:26
S12	224025	"438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 11:50
S13	15	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613") and 'mosfet' and 'dielectric metal oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/15 10:49
S14	4906	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613") and 'mosfet' and 'dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/15 10:51
S15	73	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613") and 'mosfet' and 'dielectric') and 'hafnium'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 15:23
S16	24	((("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613") and 'mosfet' and 'dielectric') and 'hafnium') and 'lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/15 10:55
S17	2	("6020024").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/02/15 11:22
S18	4	("4432035").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/02/15 13:44
S19	417	(257/411).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/12 14:07

S20	5	("257/411").CCLS.) and 'hafnium' and 'lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/02/15 13:46
S21	230368	"438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 11:54
S22	168	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613" ) and 'hafnium' and 'lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/23 12:14
S23	2	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613" ) and 'hafnium' and 'combining' with 'oxygen'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 12:02
S24	91	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613" ) and 'hafnium' with 'oxygen'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 12:07
S25	67	'hafnium' with 'reaction' with 'oxygen'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 12:32
S26	3	'hafnium oxide' near 'formation'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 12:33
S27	58	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613" ) and 'silicon oxide' and 'hafnium' and 'lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 15:42
S28	51	("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613" ) and 'metal' with 'reduces' with 'silicon oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 13:42
S29	199	(438/785).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/12 14:07
S30	51	((438/785).ccls. and @ad<="20010613") and 'Hf'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 14:05

S31	32	((438/785).ccls. and @ad<="20010613") and 'Hafnium'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/21 14:07
S32	4	("4432035").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/25 14:32
S33	1	"2693629".PN.	USPAT	OR	OFF	2002/06/25 14:35
S34	1	"3819990".PN.	USPAT	OR	OFF	2002/06/25 14:35
S35	1	"4062749".PN.	USPAT	OR	OFF	2002/06/25 14:38
S36	1	"4227944".PN.	USPAT	OR	OFF	2002/06/25 14:38
S37	1	"5106827".PN.	USPAT	OR	OFF	2002/06/25 15:21
S38	1	"5106827".PN.	USPAT	OR	OFF	2002/06/25 15:21
S39	1	"5187638".PN.	USPAT	OR	OFF	2002/06/25 15:21
S40	1	"5188902".PN.	USPAT	OR	OFF	2002/06/25 15:21
S41	1	"5273927".PN.	USPAT	OR	OFF	2002/06/25 15:22
S42	1	"6177361".PN.	USPAT	OR	OFF	2002/06/25 15:22
S43	1	"5824590".PN.	USPAT	OR	OFF	2002/06/25 15:22
S44	1	"5773314".PN.	USPAT	OR	OFF	2002/06/25 15:22
S45	1	"5572052".PN.	USPAT	OR	OFF	2002/06/25 15:22
S46	90	(("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010613") and 'mosfet' and 'dielectric') and 'hafnium'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 16:05
S47	0	@ad<="20010613" and 'reduces' with 'silicon dioxide to silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 15:44
S48	1028	@ad<="20010613" and 'reduces' with 'silicon dioxide' with 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 15:47
S49	29	@ad<="20010613" and 'reduces' adj 'silicon dioxide' with 'silicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 16:01
S50	4	@ad<="20010613" and 'hafnium' adj 'silicon dioxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 15:55

S51	1	@ad<="20010613" and 'hafnium' adj 'silicon oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/06 09:16
S52	126214	"438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113" and 'high dielectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/25 16:09
S53	124737	"438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113" and 'high dielectric' and 'silicon oxide' and 'hafnium'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 08:52
S54	31	@ad<="20010113" and 'PVD' with 'ion bombardment'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 11:45
S55	393	@ad<="20010113" and 'high dielectric' and 'physical vapor deposition' or 'PVD' with 'ion bombardment'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 09:01
S56	393	@ad<="20010113" and 'high dielectric' and 'physical vapor deposition' or 'PVD' with 'ion bombardment energy'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 09:04
S57	13419	@ad<="20010113" and 'high dielectric constant'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 09:08
S58	332	(@ad<="20010113" and 'high dielectric constant') and 'physical vapor deposition'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 09:09
S59	0	((@ad<="20010113" and 'high dielectric constant') and 'physical vapor deposition') and 'ion bombardment energy'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 09:10
S60	16	((@ad<="20010113" and 'high dielectric constant') and 'physical vapor deposition') and 'ion bombardment'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 09:10
S61	1	"4495219".PN.	USPAT	OR	OFF	2002/07/11 10:00
S62	1	"6013553".PN.	USPAT	OR	OFF	2002/07/11 10:00
S63	1	"6015739".PN.	USPAT	OR	OFF	2002/07/11 10:00
S64	1	"5464792".PN.	USPAT	OR	OFF	2002/07/11 10:00

S65	1	"6020024".PN.	USPAT	OR	OFF	2002/07/11 10:01
S66	1	"6020243".PN.	USPAT	OR	OFF	2002/07/11 10:01
S67	1	"6060755".PN.	USPAT	OR	OFF	2002/07/11 10:01
S68	1	"6110784".PN.	USPAT	OR	OFF	2002/07/11 10:01
S69	6	@ad<="20010113" and 'hafnium deposition'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 11:46
S70	22	@ad<="20010113" and 'hafnium' and 'PVD' and 'ion bombardment'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 11:52
S71	3	@ad<="20010113" and 'hafnium' and 'PVD' and 'ion bombardment' and 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 11:51
S72	3	@ad<="20010113" and 'hafnium' and 'sputtering' and 'ion bombardment' with 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/06 09:10
S73	53	@ad<="20010113" and 'metal' and 'sputtering' and 'ion bombardment' with 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 12:56
S74	1	"4520413".PN.	USPAT	OR	OFF	2002/07/11 13:08
S75	1	"5930611".PN.	USPAT	OR	OFF	2002/07/11 13:08
S76	1	"6054331".PN.	USPAT	OR	OFF	2002/07/11 13:09
S77	1	"6060391".PN.	USPAT	OR	OFF	2002/07/11 13:11
S78	1	"6069070".PN.	USPAT	OR	OFF	2002/07/11 13:12
S79	266	@ad<="20010113" and 'hafnium' with 'sputtering'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/11 13:15
S80	22	@ad<="20010113" and 'hafnium' and 'PVD' and 'ion bombardment'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 12:01
S81	22	@ad<="20010613" and 'hafnium' and 'PVD' and 'ion bombardment'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 12:09
S82	1	"4173661".PN.	USPAT	OR	OFF	2002/07/23 12:08
S83	1	"5773363".PN.	USPAT	OR	OFF	2002/07/23 12:08

S84	5	@ad<="20010613" and 'hafnium' and 'PVD' and 'ion bombardment' with 'energy'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 13:16
S85	6	@ad<="20010613" and 'PVD' and 'ion bombardment' with 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 12:40
S86	3	@ad<="20010613" and 'hafnium' and 'ion bombardment' with 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 12:52
S87	29	@ad<="20010613" and 'PVD' and 'oxygen radical'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 12:38
S88	67	@ad<="20010613" and 'sputter' and 'oxygen radical'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 12:39
S89	19	@ad<="20010613" and 'hafnium' and 'sputter' with 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 12:50
S90	4	@ad<="20010613" and 'hafnium' and 'sputter' and 'oxygen radical' with 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 12:44
S91	6	@ad<="20010613" and 'hafnium' and 'ionized' with 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 12:50
S92	14	@ad<="20010613" and 'hafnium' and 'ion bombardment' and 'sputter' and 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 13:01
S93	912	@ad<="20010613" and 'dielectric deposition'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 13:10
S94	118	(@ad<="20010613" and 'dielectric deposition') and 'refractory metal'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 13:09

S95	1	((@ad<="20010613" and 'dielectric deposition') and 'refractory metal') and 'sputter' and 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 13:09
S96	0	((@ad<="20010613" and 'dielectric deposition') and 'refractory metal') and 'PVD' and 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 13:09
S97	12	((@ad<="20010613" and 'dielectric deposition') and 'hafnium'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 13:09
S98	6	@ad<="20010613" and 'hafnium deposition'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 13:15
S99	96	@ad<="20010613" and 'ion bombardment' with 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 13:19
S100	3	((@ad<="20010613" and 'ion bombardment' with 'eV') and 'hafnium'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/07/23 13:20
S101	2	("6399521").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/07/23 14:33
S102	78	(("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113") and 'dielectric layer') and 'hafnium' and 'lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/23 12:15
S103	108	(("438"/\$.ccls. or "257"/\$.ccls. and @ad<="20010113") and 'dielectric layer') and 'hafnium' and 'lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/24 08:21
S104	8	@ad<="20010113" and 'dielectric layer' and 'hafnium' and 'lanthanum' and 'oxygen' and 'ion bombardment'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/24 08:33
S105	29	@ad<="20010113" and 'physical vapor deposition' and 'hafnium' and 'oxygen' and 'ion bombardment'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/24 08:39

S10 6	62	@ad<="20010113" and 'dielectric' and 'physical vapor deposition' and 'ion bombardment' same 'energy'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/24 08:40
S10 7	120	@ad<="20010113" and 'physical vapor deposition' and 'ion bombardment' same 'energy'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/24 08:40
S10 8	14	@ad<="20010113" and 'hafnium' and 'physical vapor deposition' and 'ion bombardment' same 'energy'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/24 08:53
S10 9	2	@ad<="20010113" and 'lanthanum' and 'physical vapor deposition' and 'ion bombardment' same 'energy'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/24 08:41
S11 0	14	@ad<="20010113" and 'physical vapor deposition' same 'hafnium oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/24 08:45
S11 1	4	@ad<="20010113" and 'hafnium' and 'electron beam evaporation' and 'ion bombardment' and '10 eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/24 08:59
S11 2	3	@ad<="20010113" and 'lanthanum' and 'electron beam evaporation' and 'ion bombardment' and '10 eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/24 09:37
S11 3	2	@ad<="20010113" and 'lanthanum' and 'hafnium' and 'oxygen radical'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/12/24 09:40
S11 4	2	("6387761").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/21 13:36
S11 5	2	("6159855").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/21 13:38

S11 6	2	("6013553").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/21 13:38
S11 7	2178	@ad<="20010613" and 'Hafnium' same 'Lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/21 16:05
S11 8	52	@ad<="20010613" and 'dielectric' with 'Hafnium' same 'Lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/06 09:17
S11 9	39	@ad<="20010613" and 'first' with 'Hf' same 'second' with 'La'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/21 14:42
S12 0	274	@ad<="20010613" and 'first' with 'Group IV' and 'second' with 'Group III'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/21 14:45
S12 1	16	@ad<="20010613" and 'first' with 'Group IVB' and 'second' with 'Group IIIB'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/21 15:06
S12 2	243	(438/785).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:21
S12 3	83	(438/722).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/21 15:31
S12 4	457	(257/411).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/21 15:31
S12 5	597	(257/310).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/12 14:08
S12 6	461	(257/410).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/12 14:08

S12 7	158	(438/635).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/12 14:09
S12 8	627	(438/778).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/12 14:10
S12 9	400	(438/758).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/12 14:10
S13 0	457	(257/411).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:22
S13 1	631	(438/240).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:23
S13 2	102	(438/216).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/12 14:11
S13 3	275	(438/591).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:23
S13 4	739	(438/585).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/12 14:13
S13 5	170	@ad<="20010613" and 'Hafnium oxide' with 'Lanthanum oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/06 09:11
S13 6	2	"20010013629"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/05 14:41
S13 7	2	"20020192974"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/05 14:41

S13 8	65	@ad<="20010613" and 'silicon oxide' with 'Hafnium' with 'Lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/06 09:05
S13 9	4	(("6159855") or ("6013553")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/11/06 09:05
S14 0	3	@ad<="20010113" and 'hafnium' and 'sputtering' and 'ion bombardment' with 'eV'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/06 09:10
S14 1	39	@ad<="20010613" and 'MOS' and 'Hafnium oxide' with 'Lanthanum oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/06 09:11
S14 2	2	@ad<="20010613" and 'hafnium' adj 'silicon oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/11/06 09:16
S14 3	58	@ad<="20010613" and 'dielectric' with 'Hafnium' same 'Lanthanum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:10
S14 4	106	(438/722).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/12 14:07
S14 5	593	(257/411).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/04/12 14:08
S14 6	259	(438/785).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/12 14:08
S14 7	629	(257/310).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:22

S14 8	482	(257/410).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:22
S14 9	660	(438/778).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:22
S15 0	434	(438/758).CCLS. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:22
S15 1	114	(438/216).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:23
S15 2	287	(438/591).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/04/12 14:13
S15 3	760	(438/585).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:23
S15 4	671	(438/240).ccls. and @ad<="20010613"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/12 14:23
S15 5	14	("6784508") or ("6679996") or ("6348373") or ("6573160") or ("6495474") or ("6713846") or ("6407435").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/13 12:19
S15 6	2	("20020190302").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/13 11:09
S15 7	2	("20020106536").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/13 11:09

S15 8	2	("6573197").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/13 12:38
S15 9	2	("6184072").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/13 12:38
S16 0	1043	@ad<="20010613" and 'Hafnium' same 'Lanthanum' same 'oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:11
S16 1	192	@ad<="20010613" and 'Hafnium oxide' same 'Lanthanum oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:44
S16 2	1	"20020173130".PN.	US-PGPUB	OR	ON	2005/01/21 15:17
S16 3	1	"6451641".PN.	USPAT; USOCR	OR	ON	2005/01/21 15:18
S16 4	1	"6335238".PN.	USPAT; USOCR	OR	ON	2005/01/21 15:18
S16 5	1142	'high dielectric' with 'metal oxides'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:57
S16 6	56	'high dielectric' with 'metal oxides' with 'hafnium'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 16:31
S16 7	1	"20020195610".PN.	US-PGPUB	OR	ON	2005/01/21 16:07
S16 8	1	"20020145168".PN.	US-PGPUB	OR	ON	2005/01/21 16:07
S16 9	1	"20020140012".PN.	US-PGPUB	OR	ON	2005/01/21 16:07
S17 0	1	"20020131675".PN.	US-PGPUB	OR	ON	2005/01/21 16:07
S17 1	1	"20010013313".PN.	US-PGPUB	OR	ON	2005/01/21 16:07
S17 2	2	("5365096").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 16:31

S17 3	2	("6495474").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/24 09:31
S17 4	1	"6184072".PN.	USPAT; USOCR	OR	ON	2005/01/24 09:31
S17 5	2	("6713846").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/24 09:32
S17 6	1	"6479404".PN.	USPAT; USOCR	OR	ON	2005/01/24 09:33
S17 7	1	"6407435".PN.	USPAT; USOCR	OR	ON	2005/01/24 09:35
S17 8	1	"6383873".PN.	USPAT; USOCR	OR	ON	2005/01/24 09:35